

| | | | |
|-------------------|-------|-----|-----|
| N-channel MOS-FET | | | |
| 700V | 1,85Ω | ±5A | 60W |

2SK2695-01

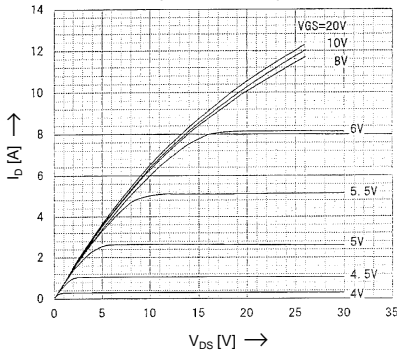
FAP-IIIB Series



> Characteristics

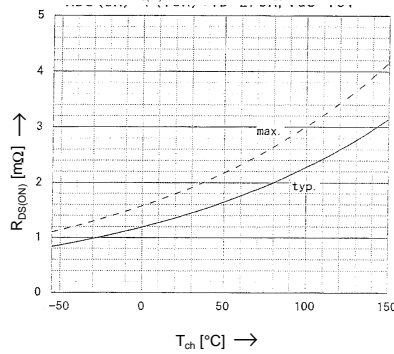
Typical Output Characteristics

$I_D = f(V_{DS})$; 80μs pulse test; $T_{ch} = 25^\circ\text{C}$



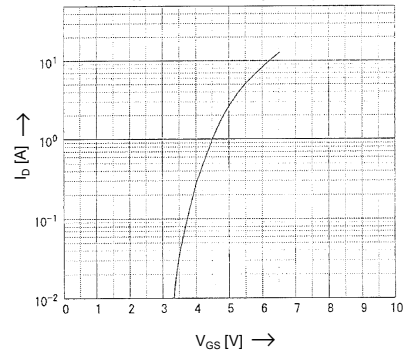
Drain-Source On-State Resistance vs. T_{ch}

$R_{DS(on)} = f(T_{ch})$; $I_D = 2.5\text{A}$; $V_{GS} = 10\text{V}$



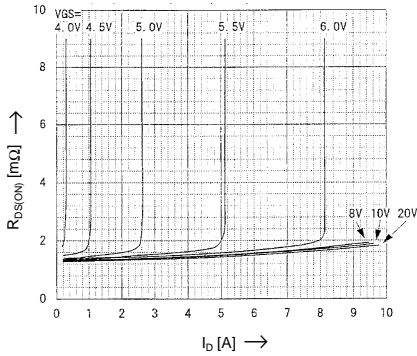
Typical Transfer Characteristics

$I_D = f(V_{GS})$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



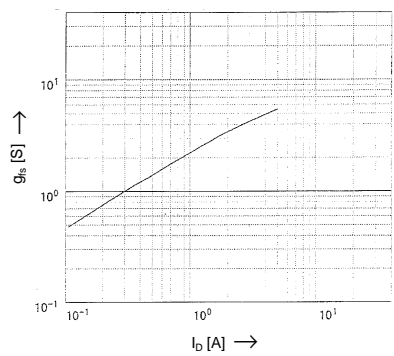
Typical Drain-Source On-State-Resistance vs. I_D

$R_{DS(on)} = f(I_D)$; 80μs pulse test; $T_{ch} = 25^\circ\text{C}$



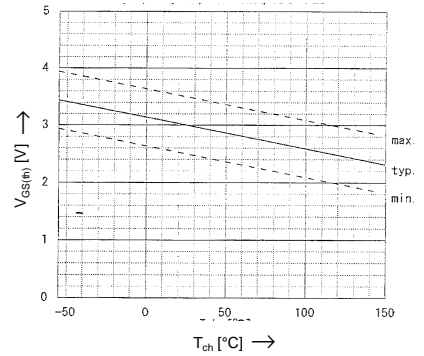
Typical Forward Transconductance vs. I_D

$g_{fs} = f(I_D)$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



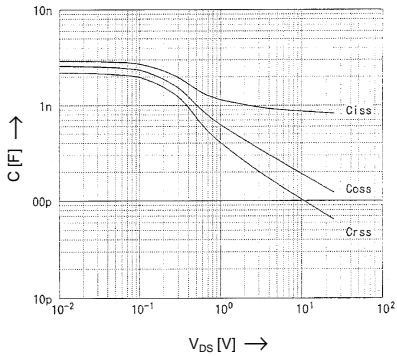
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)} = f(T_{ch})$; $I_D = 1\text{mA}$; $V_{DS} = V_{GS}$



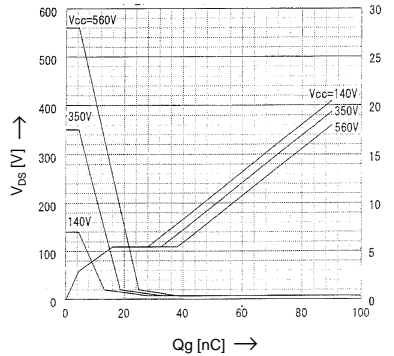
Typical Capacitances vs. V_{DS}

$C = f(V_{DS})$; $V_{GS} = 0\text{V}$; $f = 1\text{MHz}$



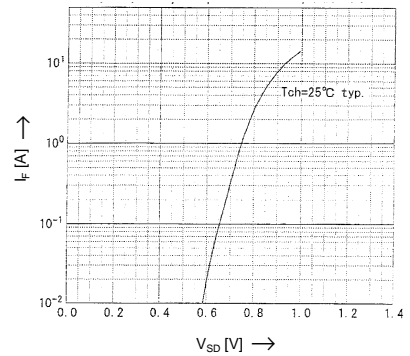
Typical Gate Charge Characteristic

$V_{GS} = f(Q_g)$; $I_D = 5\text{A}$; $T_{ch} = 25^\circ\text{C}$



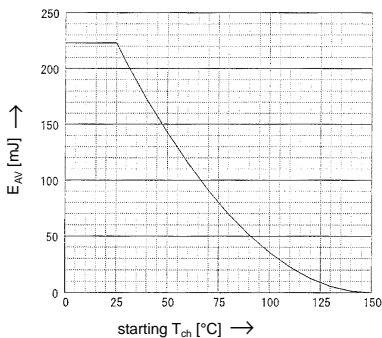
Forward Characteristics of Reverse Diode

$I_F = f(V_{SD})$; 80μs pulse test; $V_{GS} = 0\text{V}$



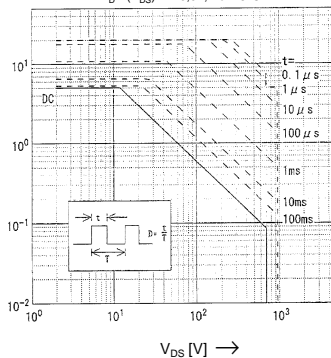
Maximum Avalanche Energy vs. starting T_{ch}

$E_{AV} = f(\text{starting } T_{ch})$; $V_{CC} = 24\text{V}$; $I_{AV} \leq 45\text{A}$



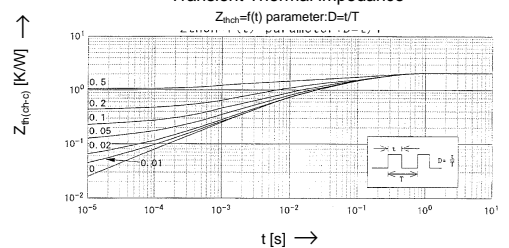
Safe Operation Area

$I_D = f(V_{DS})$; $D = 0.01$; $T_{ch} = 25^\circ\text{C}$



Transient thermal impedance

$Z_{th(ch-c)} = f(t)$ parameter: $D = t/T$



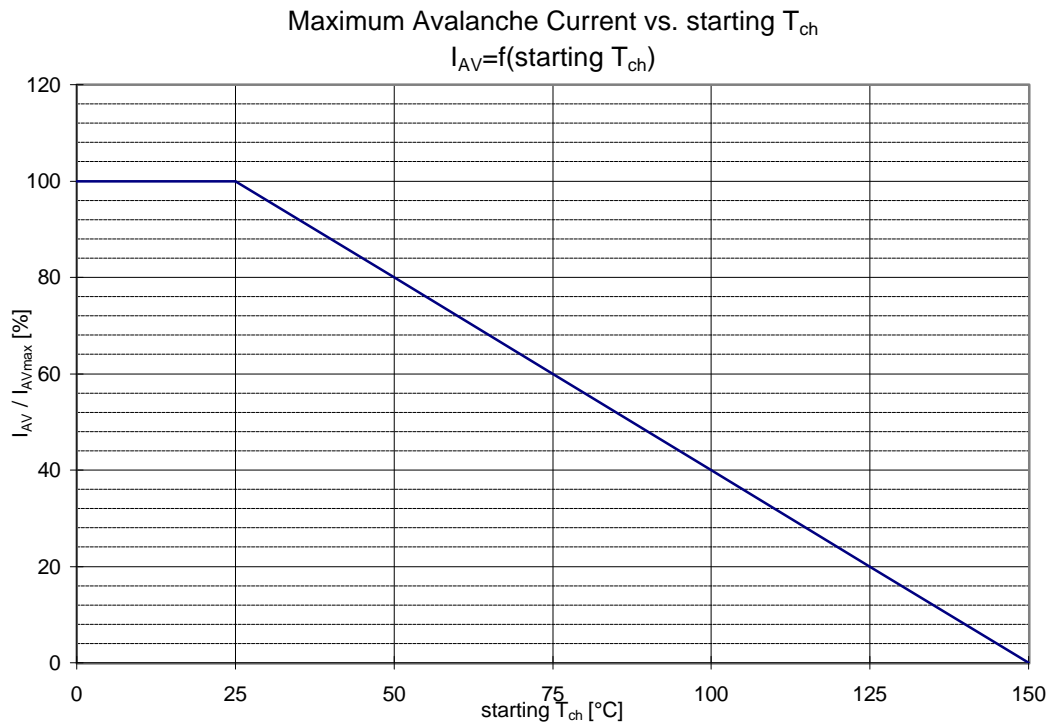
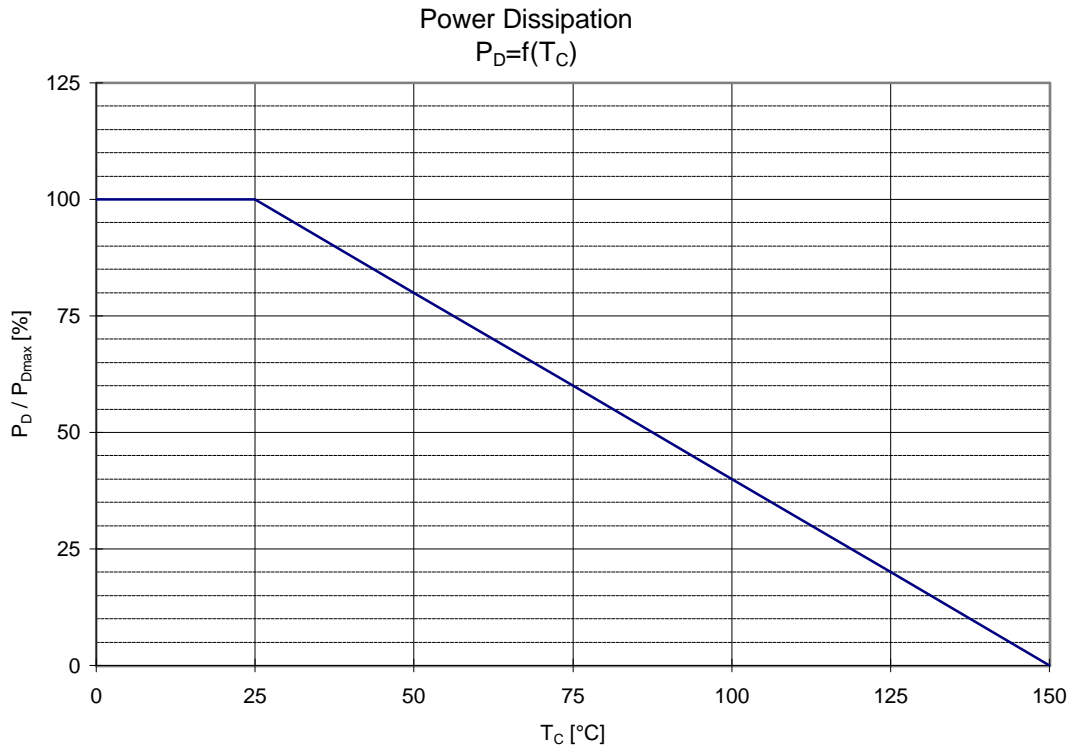
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| 700V | 1,85Ω | ±5A | 60W |

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Datasheets for electronics components.